

Vishay Semiconductors

RoHS COMPLIANT

HALOGEN

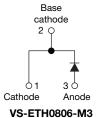
FREE

Hyperfast Rectifier, 8 A FRED Pt®





2L TO-220 FULL-PAK





VS-ETH0806FP-M3

PRODUCT SUMMARY					
Package	2L TO-220AC, 2L TO-220FP				
I _{F(AV)}	8 A				
V_{R}	600 V				
V _F at I _F	1.3 V				
t _{rr} (typ.)	16 ns				
T _J max.	175 °C				
Diode variation	Single die				

FEATURES

- · Hyperfast soft recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V_{RRM}		600	V		
Average rectified forward current in	I	T _C = 146 °C	8	А		
DC FULL-PAK	I _{F(AV)}	T _C = 114 °C	0			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	80			
Repetitive peak surge current		T _C = 137 °C	16	А		
Square wave 20 kHz duty cycle (50 %) FULL-PAK	I _{FRM}	T _C = 96 °C	10			
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. M				UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	$I_R = 100 \mu A$	600	ı	ı		
Forward voltage	V _F	I _F = 8 A	-	2.0	2.65	7 V	
		I _F = 8 A, T _J = 150 °C	-	1.3	1.85		
Reverse leakage current I _R		$V_R = V_R$ rated	-	0.02	12		
		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	15	100	μA	
Junction capacitance	C _T	V _R = 600 V	-	6	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	16	23	
Payaraa raaayan tima	+	$I_F = 8 \text{ A}, dI_F/dt = 100$	$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		20	28	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	21	-	ns
		T _J = 125 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 390 \text{ V}$	-	39	-	
Peak recovery current	1	T _J = 25 °C		-	3	-	Α
reak recovery current	I _{RRM}	T _J = 125 °C		-	5	-	_ A
Doverson vaccioni, chevac	0	T _J = 25 °C		-	36	-	
Reverse recovery charge	Q _{rr}	T _J = 125 °C	125 °C		108	-	nC
Reverse recovery time	t _{rr}	I _F = 8 A		-	30	-	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	$dI_F/dt = 600 A/\mu s$	-	13	=	Α
Reverse recovery charge	Q _{rr}	V _R = 390 V		-	205	=	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance,	D		-	2.0	2.6		
junction to case FULL-PAK	R_{thJC}		-	4.6	5.5		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
\\/-:- -t			-	2	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)	
Madring dovice		Case style 2L TO-220AC	ETH0806		•		
Marking device		Case style 2L TO-220 FULL-PAK		ETH0	806FP		

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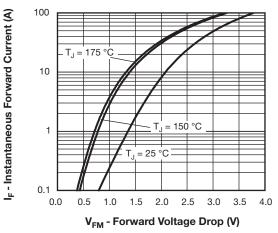


Fig. 1 - Typical Forward Voltage Drop Characteristics

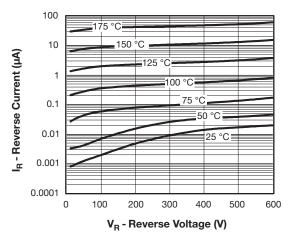


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

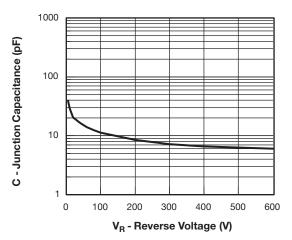


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

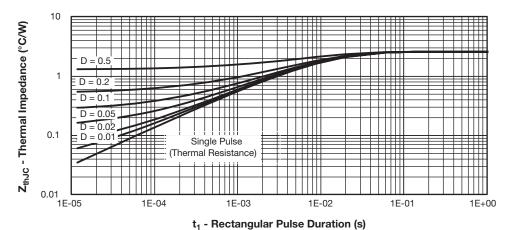


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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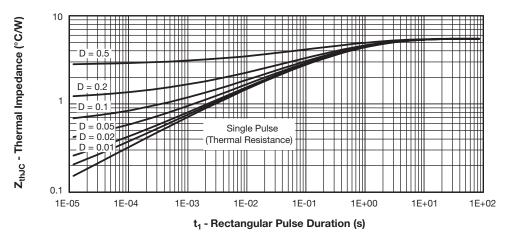


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

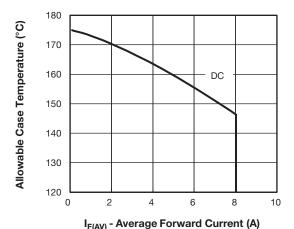
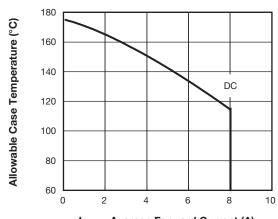
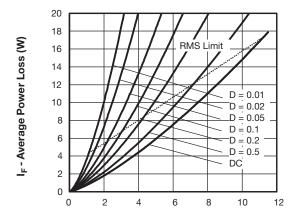


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current



I_{F(AV)} - Average Forward Current (A)

Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)



I_{F(AV)} - Average Forward Current (A)
Fig. 8 - Forward Power Loss Characteristics

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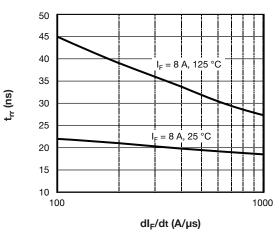


Fig. 9 - Typical Reverse Recovery vs. dl_F/dt

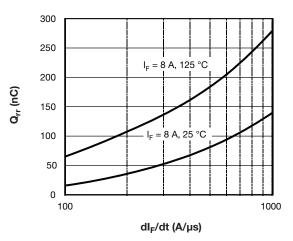


Fig. 10 - Typical Stored Charge vs. dl_F/dt

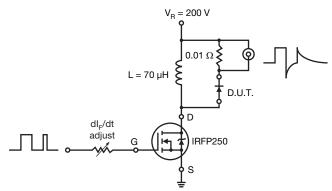
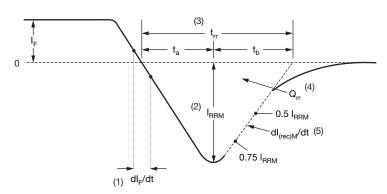


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

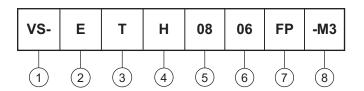
Fig. 12 - Reverse Recovery Waveform and Definitions

VS-ETH0806-M3, VS-ETH0806FP-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Circuit configuration:

E = single diode

3 - T = TO-220

H = hyperfast recovery time

Current code: 08 = 8 A

Voltage code: 06 = 600 V

7 - • None = TO-220

• FP = FULL-PAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant and terminations lead (Pb)-free

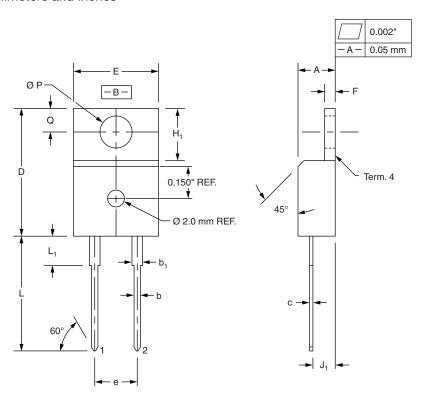
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-ETH0806-M3	50	1000	Antistatic plastic tube			
VS-ETH0806FP-M3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS					
Dimensions	2L TO-220AC	www.vishay.com/doc?95259			
Dimensions	2L TO-220 FULL-PAK	www.vishay.com/doc?95260			
Dank manufacture information	2L TO-220AC	www.vishay.com/doc?95391			
Part marking information	2L TO-220 FULL-PAK	www.vishay.com/doc?95392			

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True 2 Pin TO-220

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	METERS	INC	HES
STMBOL	MIN.	MAX.	MIN.	MAX.
А	4.32	4.57	0.170	0.180
b	0.71	0.91	0.028	0.036
b ₁	1.15	1.39	0.045	0.055
С	0.36	0.53	0.014	0.021
D	14.99	15.49	0.590	0.610
E	10.04	10.41	0.395	0.410
е	5.08	BSC	0.200	BSC
F	1.22	1.37	0.048	0.054
H ₁	5.97	6.47	0.235	0.255
J ₁	2.54	2.79	0.100	0.110
L	13.47	13.97	0.530	0.550
L ₁ (1)	3.31	3.81	0.130	0.150
Ø P	3.79	3.88	0.149	0.153
Q	2.60	2.84	0.102	0.112

Notes

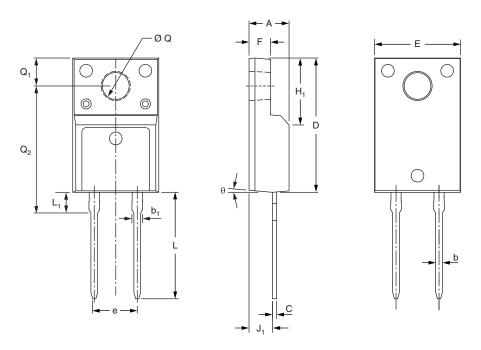
- $^{(1)}$ Lead dimension and finish uncontrolled in L_1
- These dimensions are within allowable dimensions of JEDEC TO-220AB rev. J outline dated 3-24-87
- Controling dimension: Inch



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True 2 Pin TO-220 FULL-PAK

DIMENSIONS in millimeters and inches



CYMPOL	MILLIM	METERS	INCH	IES
SYMBOL	MIN.	MAX.	MIN.	MAX.
A	4.53	4.93	0.178	0.194
b	0.71	0.91	0.028	0.036
b ₁	1.15	1.39	0.045	0.055
С	0.36	0.53	0.014	0.021
D	15.67	16.07	0.617	0.633
E	9.96	10.36	0.392	0.408
е	5.08 t	ypical	0.200 ty	ypical
F	2.34	2.74	0.092	0.107
H ₁	6.50	6.90	0.256	0.272
J ₁	2.56	2.96	0.101	0.117
L	12.78	13.18	0.503	0.519
L ₁	2.23	2.63	0.088	0.104
ØQ	2.98	3.38	0.117	0.133
Q ₁	3.10	3.50	0.122	0.138
Q_2	14.80	15.20	0.583	0.598
θ	0°	5°	0°	5°



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Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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